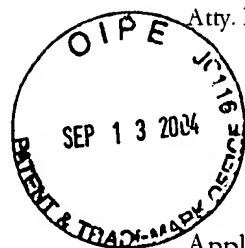


J Kw

Patent

Atty. Dkt. No.: 124263-1019  
UTA No. 013-03 CIP



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application. No. : 10/822,345  
First Named Inventor : Meng Tao  
Filed : April 12, 2004  
Title : IMPROVEMENTS FOR SEMICONDUCTOR INTERFACES  
Art Unit : 2813  
Examiner : Not Yet Assigned

Certificate of Mailing Under 37 CFR 1.8

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Sir:

Pursuant to the provisions of 37 C.F.R. § 1.97, Applicants hereby make of record the references set forth in the attached form PTO/SB/08B. No inference should be made that the cited references are in fact material, are in fact prior art, or that no better art exists. The cited references are listed in numerical order and not in any order based on their pertinence.

It is requested that the Examiner fully consider the cited references and that they be cited on the front of any patent issuing from this application.

Copies of the cited references are attached.

An early action on the merits is respectfully requested.

Respectfully submitted,

Date: Sept 8, 2004

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Application Number	10/822,345
Filing Date	April 12, 2004
First Named Inventor	Meng Tao
Group Art Unit	2812
Examiner Name	Not Yet Assigned
Attorney Docket Number	124263-1019

**OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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